



PTO/SB/08a/b (08-03)

Approved for use through 07/31/2008. OMB 0651-0031

U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Project Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

<b>Substitute for form 1449A/B/PTO</b>  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use as many sheets as necessary)			<b>Complete if Known</b>		
			Application Number	10/660,602-Conf. #7883	
			Filing Date	September 12, 2003	
			First Named Inventor	John T. Moore	
			Art Unit	2811 2924	
			Examiner Name	Not Yet Assigned C. Wilson	
Sheet	1	of	1	Attorney Docket Number	M4065.0693/P693-A

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>3</sup>
		Country Code <sup>2</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)				

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. <sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
aw	CA	KAWAMOTO, Yoji And NISHIDA, Masaru, IONIC CONDUCTION IN As <sub>2</sub> S <sub>3</sub> -Ag <sub>2</sub> S, GeS <sub>2</sub> -GeS-Ag <sub>2</sub> S AND P <sub>2</sub> S <sub>5</sub> -Ag <sub>2</sub> S GLASSES, Journal of Non-Crystalline Solids 20 (1976) 393-404.	

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached.

Christian Wilson

5/17/04

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)				<b>Complete if Known</b>	
				Application Number	To be assigned 10/660602
				Filing Date	Currently Herewith 9/12/03
				First Named Inventor	John T. Moore
				Art Unit	2824
				Examiner Name	M. Luhrs C. WILSON
Sheet	1	of	10	Attorney Docket Number	M4065.0693/P693-A

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)				
CDW	AA	2002/0000666		1/3/2002	Kozicki et al.	
	AB	2002/0168820 App.		11/2002	Kozicki	
	AC	2000/0072188 App		6/2002	Gilton	
	AD	2002/0123169 App		9/2002	Moore et al.	
	AE	2002/0123248 App.		9/2002	Moore et al.	
	AF	2003/0027416 A1		2/2003	Moore et al.	
	AG	2003/0049912 A1		3/2003	Campbell et al.	
	AH	2003/0045054 A1		3/2003	Campbell et al.	
	AI	2003/0045049 A1		3/2003	Campbell et al.	
	AJ	2003/0143782 A1		7/2003	Gilton et al.	
	AK	2003/0050124 A1		3/2003	Kanamaru et al.	
	AL	2003/0107105 A1		6/2003	Kozicki	
	AM	2003/0137869 A1		7/2003	Kozicki	
	AN	3,622,319		11/1971	Sharp	
	AO	3,743,847		7/1973	Boland	
	AP	4,269,935		5/1981	Masters et al.	
	AQ	4,312,938		1/1982	Drexler, et al.	
	AR	4,316,946		1/1982	Masters, et al.	
	AS	4,320,191		3/1982	Yoshikawa et al.	
	AT	4,405,710		9/1983	Balasubramanyam et al.	
	AU	4,419,421		12/1983	Wichelhaus, et al.	
	AV	4,795,657		1/1989	Formigoni et al.	
	AW	4,847,674		7/1989	Sliwa et al.	
	AX	4,499,557		2/1985	Holmberg et al.	
	AY	5,177,567		1/1993	Klersy et al.	
	AZ	5,219,788		6/1993	Abernathey et al.	
	AA1	5,238,862		8/1993	Blalock et al.	
	AB1	5,315,131		5/1994	Kishimoto et al.	
	AC1	5,350,484		9/1994	Gardner et al.	
	AD1	5,360,981		11/1994	Owen et al.	
	AE1	5,500,532		3/19/1996	Kozicki et al.	
	AF1	5,512,328		4/1996	Yoshimura et al.	
	AG1	5,512,773		4/1996	Wolf et al.	
	AH1	5,726,083		3/1998	Takaishi	
	AI1	5,751,012		5/12/1998	Wolstenholme et al.	
	AJ1	5,761,115		6/1998	Kozicki et al.	
	AK1	5,789,277		8/1998	Zahorik et al.	
	AL1	5,841,150		11/1998	Gonzalez et al.	
	AM1	5,846,889		12/1998	Harbison et al.	
	AN1	5,896,312		4/20/1999	Kozicki et al.	
	AO1	5,914,893		6/22/1999	Kozicki et al.	
	AP1	5,920,788		7/1999	Reinberg	
	AQ1	5,998,066		12/1999	Block et al.	
8	AR1	6,077,729		6/2000	Harshfield	

Christa Wilson

5/11/04

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

[illegible]

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
AW	BA	56126916	10/19981	Akira et al.		
J	BB	WO 02/21542	03/14/2002	Kozicki et al.		
	BC	WO 00/48196	08/17/2000	Kozicki et al.		
	BD	WO 97/48032	12/18/1997	Kozicki et al.		
BE	WO 99/28914	06/10/1999	Kozicki et al.			

Examiner Signature	Christa Wilson	Date Considered	5/11/04
-----------------------	----------------	--------------------	---------

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> See attached Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 801.04. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 18 if possible. <sup>6</sup> Applicant is to place a check mark here if English language Translation is attached.

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449B/PTO		<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		Application Number	To be assigned to 660602
		Filing Date	Currently Herewith 9/12/03
		First Named Inventor	John T. Moore
		Prior Group Art Unit	2824
		Prior Examiner Name	M. Luhrs C. Wilson
		Attorney Docket Number	M4065.0693/P693-A
Sheet	3	of	10

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
SW	CA	Abdel-Ail, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge <sub>5</sub> As <sub>38</sub> Te <sub>57</sub> chalcogenide glass, Vacuum 59 (2000) 845-853.	
	CB	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-1189.	
	CC	Adler, D.; Henisch, H.K.; Mott, S.N., The mechanism of threshold switching in amorphous alloys, Rev. Mod. Phys. 50 (1978) 209-220.	
	CD	Afifi, M.A.; Labib, H.H.; El-Fazary, M.H.; Fadel, M., Electrical and thermal properties of chalcogenide glass system Se <sub>75</sub> Ge <sub>25</sub> -xSb <sub>x</sub> , Appl. Phys. A 55 (1992) 167-169.	
	CE	Afifi, M.A.; Labib, H.H.; Fouad, S.S.; El-Shazly, A.A., Electrical & thermal conductivity of the amorphous semiconductor GexSe <sub>1-x</sub> , Egypt. J. Phys. 17 (1986) 335-342.	
	CF	Alekperova, Sh.M.; Gadzhieva, G.S., Current-Voltage characteristics of Ag <sub>2</sub> Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.	
	CG	Aleksiejunas, A.; Cesnys, A., Switching phenomenon and memory effect in thin-film heterojunction of polycrystalline selenium-silver selenide, Phys. Stat. Sol. (a) 19 (1973) K169-K171.	
	CH	Angell, C.A., Mobile ions in amorphous solids, Annu. Rev. Phys. Chem. 43 (1992) 693-717.	
	CI	Aniya, M., Average electronegativity, medium-range-order, and ionic conductivity in superionic glasses, Solid state Ionics 136-137 (2000) 1085-1089.	
	CJ	Asahara, Y.; Izumitani, T., Voltage controlled switching in Cu-As-Se compositions, J. Non-Cryst. Solids 11 (1972) 97-104.	
	CK	Asokan, S.; Prasad, M.V.N.; Parthasarathy, G.; Gopal, E.S.R., Mechanical and chemical thresholds in IV-VI chalcogenide glasses, Phys. Rev. Lett. 62 (1989) 808-810	
	CL	Axon Technologies Corporation, TECHNOLOGY DESCRIPTION: Programmable Metalization Cell(PMC), pp. 1-6 (Pre-May 2000).	
	CM	Baranovskii, S.D.; Cordes, H., On the conduction mechanism in ionic glasses, J. Chem. Phys. 111 (1999) 7546-7557.	
	CN	Belin, R.; Taillades, G.; Pradel, A.; Ribes, M., Ion dynamics in superionic chalcogenide glasses: complete conductivity spectra, Solid state Ionics 136-137 (2000) 1025-1029.	
	CO	Belin, R.; Zerouale, A.; Pradel, A.; Ribes, M., Ion dynamics in the argyrodite compound Ag <sub>7</sub> GeSe <sub>5</sub> I: non-Arrhenius behavior and complete conductivity spectra, Solid State Ionics 143 (2001) 445-455.	
	CP	Benmore, C.J.; Salmon, P.S., Structure of fast ion conducting and semiconducting glassy chalcogenide alloys, Phys. Rev. Lett. 73 (1994) 264-267.	
	CQ	Bernede, J.C., Influence du metal des electrodes sur les caracteristiques courant-tension des structures M-Ag <sub>2</sub> Se-M, Thin solid films 70 (1980) L1-L4.	
	CR	Bernede, J.C., Polarized memory switching in MIS thin films, Thin Solid Films 81 (1981) 155-160.	
	CS	Bernede, J.C., Switching and silver movements in Ag <sub>2</sub> Se thin films, Phys. Stat. Sol. (a) 57 (1980) K101-K104.	
	CT	Bernede, J.C.; Abachi, T., Differential negative resistance in metal/insulator/metal structures with an upper bilayer electrode, Thin solid films 131 (1985) L61-L64.	
	CU	Bernede, J.C.; Conan, A.; Fousenan't, E.; El Bouchairi, B.; Goureaux, G., Polarized memory switching effects in Ag <sub>2</sub> Se/Se/M thin film sandwiches, Thin solid films 97 (1982) 165-171.	
	CV	Bernede, J.C.; Khelil, A.; Kettaf, M.; Conan, A., Transition from S- to N-type differential negative resistance in Al-Al <sub>2</sub> O <sub>3</sub> -Ag <sub>2</sub> -xSe <sub>1+x</sub> thin film structures, Phys. Stat. Sol. (a) 74 (1982) 217-224.	
SW	CW	Bondarev, V.N.; Pikhitsa, P.V., A dendrite model of current instability in RbAg <sub>4</sub> I <sub>5</sub> , Solid State	

Christian Wilson

5/11/04

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449B/PTO		<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		Application Number	To be assigned to 660602
		Filing Date	Currently Herewith 9/12/03
		First Named Inventor	John T. Moore
		Prior Group Art Unit	2824
		Prior Examiner Name	M. Luhrs- C. Wilson
		Attorney Docket Number	M4065.0693/P693-A
Sheet	4	of	10

		Ionics 70/71 (1994) 72-76.	
du	CX	Boolchand, P., The maximum in glass transition temperature (T <sub>g</sub> ) near x=1/3 in GexSe1-x Glasses, Asian Journal of Physics (2000) 9, 709-72.	
	CY	Boolchand, P.; Bresser, W.J., Mobile silver ions and glass formation in solid electrolytes, Nature 410 (2001) 1070-1073.	
	CZ	Boolchand, P.; Georgiev, D.G.; Goodman, B., Discovery of the Intermediate Phase in Chalcogenide Glasses, J. Optoelectronics and Advanced Materials, 3 (2001), 703	
	CA1	Boolchand, P.; Selvanathan, D.; Wang, Y.; Georgiev, D.G.; Bresser, W.J., Onset of rigidity in steps in chalcogenide glasses, Properties and Applications of Amorphous Materials, M.F. Thorpe and Tichy, L. (eds.) Kluwer Academic Publishers, the Netherlands, 2001, pp. 97-132.	
	CB1	Boolchand, P.; Enzweiler, R.N.; Tenhover, M., Structural ordering of evaporated amorphous chalcogenide alloy films: role of thermal annealing, Diffusion and Defect Data Vol. 53-54 (1987) 415-420.	
	CC1	Boolchand, P.; Grothaus, J.; Bresser, W.J.; Suranyi, P., Structural origin of broken chemical order in a GeSe2 glass, Phys. Rev. B 25 (1982) 2975-2978.	
	CD1	Boolchand, P.; Grothaus, J.; Phillips, J.C., Broken chemical order and phase separation in GexSe1-x glasses, Solid state comm. 45 (1983) 183-185.	
	CE1	Boolchand, P., Bresser, W.J., Compositional trends in glass transition temperature (T <sub>g</sub> ), network connectivity and nanoscale chemical phase separation in chalcogenides, Dept. of ECECS, Univ. Cincinnati (October 28, 1999) 45221-0030.	
	CF1	Boolchand, P.; Grothaus, J., Molecular Structure of Melt-Quenched GeSe2 and GeS2 glasses compared, Proc. Int. Conf. Phys. Semicond. (Eds. Chadi and Harrison) 17 <sup>th</sup> (1985) 833-36.	
	CG1	Bresser, W.; Boolchand, P.; Suranyi, P., Rigidity percolation and molecular clustering in network glasses, Phys. Rev. Lett. 56 (1986) 2493-2496.	
	CH1	Bresser, W.J.; Boolchand, P.; Suranyi, P.; de Neufville, J.P., Intrinsically broken chalcogen chemical order in stoichiometric glasses, Journal de Physique 42 (1981) C4-193-C4-196.	
	CI1	Bresser, W.J.; Boolchand, P.; Suranyi, P.; Hernandez, J.G., Molecular phase separation and cluster size in GeSe2 glass, Hyperfine Interactions 27 (1986) 389-392.	
	CJ1	Cahen, D.; Gilet, J.-M.; Schmitz, C.; Chernyak, L.; Gartsman, K.; Jakubowicz, A., Room-Temperature, electric field induced creation of stable devices in CuInSe2 Crystals, Science 258 (1992) 271-274.	
	CK1	Chatterjee, R.; Asokan, S.; Titus, S.S.K., Current-controlled negative-resistance behavior and memory switching in bulk As-Te-Se glasses, J. Phys. D: Appl. Phys. 27 (1994) 2624-2627.	
	CL1	Chen, C.H.; Tai, K.L., Whisker growth induced by Ag photodoping in glassy GexSe1-x films, Appl. Phys. Lett. 37 (1980) 1075-1077.	
	CM1	Chen, G.; Cheng, J., Role of nitrogen in the crystallization of silicon nitride-doped chalcogenide glasses, J. Am. Ceram. Soc. 82 (1999) 2934-2936.	
	CN1	Chen, G.; Cheng, J.; Chen, W., Effect of Si3N4 on chemical durability of chalcogenide glass, J. Non-Cryst. Solids 220 (1997) 249-253.	
	CO1	Cohen, M.H.; Neale, R.G.; Paskin, A., A model for an amorphous semiconductor memory device, J. Non-Cryst. Solids 8-10 (1972) 885-891.	
	CP1	Croitoru, N.; Lazarescu, M.; Popescu, C.; Telnic, M.; and Vescan, L., Ohmic and non-ohmic conduction in some amorphous semiconductors, J. Non-Cryst. Solids 8-10 (1972) 781-786.	
	CQ1	Daiven, R.; Gill, R., Electrical properties of beta-Ag2Te and beta-Ag2Se from 4.2 to 300K, J. Appl. Phys. 38 (1967) 753-756.	
	CR1	Das et al., Theory of the characteristic curves of the silver chalcogenide glass inorganic photoresists, 54 Appl. Phys. Lett., No. 18, pp. 1745-1747 (May 1989).	
	CS1	Davis, E.A., Semiconductors without form, Search 1 (1970) 152-155.	
	CT1	Dearnaley, G.; Stoneham, A.M.; Morgan, D.V., Electrical phenomena in amorphous oxide films, Rep. Prog. Phys. 33 (1970) 1129-1191.	
du	CU1	Dejus, R.J.; Susman, S.; Volin, K.J.; Montague, D.G.; Price, D.L., Structure of Vitreous Ag-Ge-Se, J. Non-Cryst. Solids 143 (1992) 162-180.	

Christian Wilson

5/11/04

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449B/PTO		<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		Application Number	<del>To be assigned</del> 10/660602
		Filing Date	Currently Herewith 9/12/03
		First Named Inventor	John T. Moore
		Prior Group Art Unit	2824
		Prior Examiner Name	M. Luhrs C. Wilson
		Attorney Docket Number	M4065.0693/P693-A
Sheet	5	of	10

CV1	den Boer, W., Threshold switching in hydrogenated amorphous silicon, Appl. Phys. Lett. 40 (1982) 812-813.
CW1	Drusedau, T.P.; Panckow, A.N.; Klabunde, F., The hydrogenated amorphous silicon/nanodisperse metal (SIMAL) system-Films of unique electronic properties, J. Non-Cryst. Solids 198-200 (1996) 829-832.
CX1	El Bouchairi, B.; Bernede, J.C.; Burgaud, P., Properties of Ag <sub>2</sub> -xSe <sub>1+x</sub> n-Si diodes, Thin Solid Films 110 (1983) 107-113.
CY1	El Gharras, Z.; Bourahla, A.; Vautier, C., Role of photoinduced defects in amorphous Ge <sub>x</sub> Se <sub>1-x</sub> photoconductivity, J. Non-Cryst. Solids 155 (1993) 171-179.
CZ1	El Ghrandi, R.; Calas, J.; Galibert, G.; Averous, M., Silver photodissolution in amorphous chalcogenide thin films, Thin Solid Films 218 (1992) 259-273.
CA2	El Ghrandi, R.; Calas, J.; Galibert, G., Ag dissolution kinetics in amorphous GeSe <sub>5.5</sub> thin films from "in-situ" resistance measurements vs time, Phys. Stat. Sol. (a) 123 (1991) 451-460.
CB2	El-kady, Y.L., The threshold switching in semiconducting glass Ge <sub>21</sub> Se <sub>17</sub> Te <sub>62</sub> , Indian J. Phys. 70A (1996) 507-516.
CC2	Elliott, S.R., A unified mechanism for metal photodissolution in amorphous chalcogenide materials, J. Non-Cryst. Solids 130 (1991) 85-97.
CD2	Elliott, S.R., Photodissolution of metals in chalcogenide glasses: A unified mechanism, J. Non-Cryst. Solids 137-138 (1991) 1031-1034.
CE2	Elsamanoudy, M.M.; Hegab, N.A.; Fadel, M., Conduction mechanism in the pre-switching state of thin films containing Te As Ge Si, Vacuum 46 (1995) 701-707.
CF2	El-Zahed, H.; El-Korashy, A., Influence of composition on the electrical and optical properties of Ge <sub>20</sub> BixSe <sub>80-x</sub> films, Thin Solid Films 376 (2000) 236-240.
CG2	Fadel, M., Switching phenomenon in evaporated Se-Ge-As thin films of amorphous chalcogenide glass, Vacuum 44 (1993) 851-855.
CH2	Fadel, M.; El-Shair, H.T., Electrical, thermal and optical properties of Se <sub>75</sub> Ge <sub>7</sub> Sb <sub>18</sub> , Vacuum 43 (1992) 253-257.
CI2	Feng, X.; Bresser, W.J.; Boolchand, P., Direct evidence for stiffness threshold in Chalcogenide glasses, Phys. Rev. Lett. 78 (1997) 4422-4425.
CJ2	Feng, X.; Bresser, W.J.; Zhang, M.; Goodman, B.; Boolchand, P., Role of network connectivity on the elastic, plastic and thermal behavior of covalent glasses, J. Non-Cryst. Solids 222 (1997) 137-143.
CK2	Fischer-Colbrie, A.; Bienenstock, A.; Fuoss, P.H.; Marcus, M.A., Structure and bonding in photodiffused amorphous Ag-GeSe <sub>2</sub> thin films, Phys. Rev. B 38 (1988) 12388-12403.
CL2	Fleury, G.; Hamou, A.; Viger, C.; Vautier, C., Conductivity and crystallization of amorphous selenium, Phys. Stat. Sol. (a) 64 (1981) 311-316.
CM2	Fritzsche, H., Optical and electrical energy gaps in amorphous semiconductors, J. Non-Cryst. Solids 6 (1971) 49-71.
CN2	Fritzsche, H., Electronic phenomena in amorphous semiconductors, Annual Review of Materials Science 2 (1972) 697-744.
CO2	Gates, B.; Wu, Y.; Yin, Y.; Yang, P.; Xia, Y., Single-crystalline nanowires of Ag <sub>2</sub> Se can be synthesized by templating against nanowires of trigonal Se, J. Am. Chem. Soc. (2001) currently ASAP.
CP2	Gosain, D.P.; Nakamura, M.; Shimizu, T.; Suzuki, M.; Okano, S., Nonvolatile memory based on reversible phase transition phenomena in telluride glasses, Jap. J. Appl. Phys. 28 (1989) 1013-1018.
CQ2	Guin, J.-P.; Rouxel, T.; Keryvin, V.; Sangleboeuf, J.-C.; Serre, I.; Lucas, J., Indentation creep of Ge-Se chalcogenide glasses below T <sub>g</sub> : elastic recovery and non-Newtonian flow, J. Non-Cryst. Solids 298 (2002) 260-269.
CR2	Guin, J.-P.; Rouxel, T.; Sangleboeuf, J.-C.; Melscoet, I.; Lucas, J., Hardness, toughness, and scratchability of germanium-selenium chalcogenide glasses, J. Am. Ceram. Soc. 85 (2002) 1545-52.
CS2	Gupta, Y.P., On electrical switching and memory effects in amorphous chalcogenides, J. Non-

Christian Wilson

5/11/04

Substitute for form 1449B/PTO		<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		Application Number	To be assigned 10/660602
		Filing Date	Currently Here with 9/12/03
		First Named Inventor	John T. Moore
		Prior Group Art Unit	2824
		Prior Examiner Name	M. Luhrs - C. WILSON
		Attorney Docket Number	M4065.0693/P693-A
Sheet	6	of	10

CDW		Cryst. Sol. 3 (1970) 148-154.	
	CT2	Haberland, D.R.; Stiegler, H., New experiments on the charge-controlled switching effect in amorphous semiconductors, J. Non-Cryst. Solids 8-10 (1972) 408-414.	
	CU2	Haifz, M.M.; Ibrahim, M.M.; Dongol, M.; Hammad, F.H., Effect of composition on the structure and electrical properties of As-Se-Cu glasses, J. Apply. Phys. 54 (1983) 1950-1954.	
	CV2	Hajto, J.; Rose, M.J.; Osborne, I.S.; Snell, A.J.; Le Comber, P.G.; Owen, A.E., Quantization effects in metal/a-Si:H/metal devices, Int. J. Electronics 73 (1992) 911-913.	
	CW2	Hajto, J.; Hu, J.; Snell, A.J.; Turvey, K.; Rose, M., DC and AC measurements on metal/a-Si:H/metal room temperature quantised resistance devices, J. Non-Cryst. Solids 266-269 (2000) 1058-1061.	
	CX2	Hajto, J.; McAuley, B.; Snell, A.J.; Owen, A.E., Theory of room temperature quantized resistance effects in metal-a-Si:H-metal thin film structures, J. Non-Cryst. Solids 198-200 (1996) 825-828.	
	CY2	Hajto, J.; Owen, A.E.; Snell, A.J.; Le Comber, P.G.; Rose, M.J., Analogue memory and ballistic electron effects in metal-amorphous silicon structures, Phil. Mag. B 63 (1991) 349-369.	
	CZ2	Hayashi, T.; Ono, Y.; Fukaya, M.; Kan, H., Polarized memory switching in amorphous Se film, Japan. J. Appl. Phys. 13 (1974) 1163-1164.	
	CA3	Hegab, N.A.; Fadel, M.; Sedeek, K., Memory switching phenomena in thin films of chalcogenide semiconductors, Vacuum 45 (1994) 459-462.	
	CB3	Helbert et al., Intralevel hybrid resist process with submicron capability, SPIE Vol. 333 SUBMICRON LITHOGRAPHY, pp. 24-29 (1982).	
	CC3	Hill, DISSERTATION: Materials characterization of Silver Chalcogenide Programmable Metalization Cells, Arizona State University, pp. Title page-114 (UMI Company, May 1999).	
	CD3	Hirose et al., High Speed Memory Behavior and Reliability of an Amorphous As <sub>2</sub> S <sub>3</sub> Film Doped Ag, PHYS. STAT. SOL. (a) 61, pp. 87-90 (1980).	
	CE3	Hirose, Y.; Hirose, H., Polarity-dependent memory switching and behavior of Ag dendrite in Ag-photodoped amorphous As <sub>2</sub> S <sub>3</sub> films, J. Appl. Phys. 47 (1976) 2767-2772.	
	CF3	Holmquist et al., Reaction and Diffusion in Silver-Arsenic Chalcogenide Glass Systems, 62 J. AMER. CERAM. SOC., No. 3-4, pp. 183-188 (March-April 1979).	
	CG3	Hong, K.S.; Speyer, R.F., Switching behavior in II-IV-V <sub>2</sub> amorphous semiconductor systems, J. Non-Cryst. Solids 116 (1990) 191-200.	
	CH3	Hosokawa, S., Atomic and electronic structures of glassy GexSe1-x around the stiffness threshold composition, J. Optoelectronics and Advanced Materials 3 (2001) 199-214.	
	CI3	Hu, J.; Snell, A.J.; Hajto, J.; Owen, A.E., Constant current forming in Cr/p+a-Si:H/V thin film devices, J. Non-Cryst. Solids 227-230 (1998) 1187-1191.	
	CJ3	Hu, J.; Hajto, J.; Snell, A.J.; Owen, A.E.; Rose, M.J., Capacitance anomaly near the metal-non-metal transition in Cr-hydrogenated amorphous Si-V thin-film devices, Phil. Mag. B. 74 (1996) 37-50.	
	CK3	Hu, J.; Snell, A.J.; Hajto, J.; Owen, A.E., Current-induced instability in Cr-p+a-Si:H-V thin film devices, Phil. Mag. B 80 (2000) 29-43.	
	CL3	Huggett et al., Development of silver sensitized germanium selenide photoresist by reactive sputter etching in SF <sub>6</sub> , 42 APPL. PHYS. LETT., No. 7, pp. 592-594 (April 1983).	
	CM3	Iizima, S.; Sugi, M.; Kikuchi, M.; Tanaka, K., Electrical and thermal properties of semiconducting glasses As-Te-Ge, Solid State Comm. 8 (1970) 153-155.	
	CN3	Ishikawa, R.; Kikuchi, M., Photovoltaic study on the photo-enhanced diffusion of Ag in amorphous films of Ge <sub>2</sub> S <sub>3</sub> , J. Non-Cryst. Solids 35 & 36 (1980) 1061-1066.	
	CO3	Iyetomi, H.; Vashishta, P.; Kalia, R.K., Incipient phase separation in Ag/Ge/Se glasses: clustering of Ag atoms, J. Non-Cryst. Solids 262 (2000) 135-142.	
	CP3	Jones, G.; Collins, R.A., Switching properties of thin selenium films under pulsed bias, Thin Solid Films 40 (1977) L15-L18.	
CDW	CQ3	Joullie, A.M.; Marucchi, J., On the DC electrical conduction of amorphous As <sub>2</sub> S <sub>3</sub> 7 before	

Christian Wilson

2/11/04

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1448B/PTO		Complete if Known	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		Application Number	To be assigned 10/660602
		Filing Date	Currently Herewith 9/12/03
		First Named Inventor	John T. Moore
		Prior Group Art Unit	2824
		Prior Examiner Name	M. LUTTS C. WILSON
		Attorney Docket Number	M4065.0693/P693-A
Sheet	7	of	10

		switching, Phys. Stat. Sol. (a) 13 (1972) K105-K109.	
	CR3	Joullie, A.M.; Marucchi, J., Electrical properties of the amorphous alloy As <sub>2</sub> Se <sub>5</sub> , Mat. Res. Bull. 8 (1973) 433-442.	
	CS3	Kaplan, T.; Adler, D., Electrothermal switching in amorphous semiconductors, J. Non-Cryst. Solids 8-10 (1972) 538-543.	
	CT3	Kawaguchi et al., Mechanism of photosurface deposition, 164-166 J. NON-CRYST. SOLIDS, pp. 1231-1234 (1993).	
	CU3	Kawaguchi, T.; Maruno, S.; Elliott, S.R., Optical, electrical, and structural properties of amorphous Ag-Ge-S and Ag-Ge-Se films and comparison of photoinduced and thermally induced phenomena of both systems, J. Appl. Phys. 79 (1996) 9096-9104.	
	CV3	Kawaguchi, T.; Masui, K., Analysis of change in optical transmission spectra resulting from Ag photodoping in chalcogenide film, Japn. J. Appl. Phys. 26 (1987) 15-21.	
	CW3	Kawasaki, M.; Kawamura, J.; Nakamura, Y.; Aniya, M., Ionic conductivity of Ag <sub>x</sub> (GeSe <sub>3</sub> ) <sub>1-x</sub> (0<=x<=0.571) glasses, Solid state Ionics 123 (1999) 259-269.	
	CX3	Kluge, G.; Thomas, A.; Klabes, R.; Grotzschel, R., Silver photodiffusion in amorphous GexSe <sub>100-x</sub> , J. Non-Cryst. Solids 124 (1990) 186-193.	
	CY3	Kolobov, A.V., On the origin of p-type conductivity in amorphous chalcogenides, J. Non-Cryst. Solids 198-200 (1996) 728-731.	
	CZ3	Kolobov, A.V., Lateral diffusion of silver in vitreous chalcogenide films, J. Non-Cryst. Solids 137-138 (1991) 1027-1030.	
	CA4	Korkinova, Ts.N.; Andreichin, R.E., Chalcogenide glass polarization and the type of contacts, J. Non-Cryst. Solids 194 (1996) 256-259.	
	CB4	Kotkata, M.F.; Afif, M.A.; Labib, H.H.; Hegab, N.A.; Abdel-Aziz, M.M., Memory switching in amorphous GeSeTe chalcogenide semiconductor films, Thin Solid Films 240 (1994) 143-146.	
	CC4	Lakshminarayan, K.N.; Srivastava, K.K.; Panwar, O.S.; Dumar, A., Amorphous semiconductor devices: memory and switching mechanism, J. Instn Electronics & Telecom. Engrs 27 (1981) 16-19.	
	CD4	Lal, M.; Goyal, N., Chemical bond approach to study the memory and threshold switching chalcogenide glasses, Indian Journal of pure & appl. phys. 29 (1991) 303-304.	
	CE4	Leimer, F.; Stotzel, H.; Kottwitz, A., Isothermal electrical polarisation of amorphous GeSe films with blocking Al contacts influenced by Poole-Frenkel conduction, Phys. Stat. Sol. (a) 29 (1975) K129-K132.	
	CF4	Leung, W.; Cheung, N.; Neureuther, A.R., Photoinduced diffusion of Ag in GexSe <sub>1-x</sub> glass, Appl. Phys. Lett. 46 (1985) 543-545.	
	CG4	Matsushita, T.; Yamagami, T.; Okuda, M., Polarized memory effect observed on Se-SnO <sub>2</sub> system, Jap. J. Appl. Phys. 11 (1972) 1657-1662.	
	CH4	Matsushita, T.; Yamagami, T.; Okuda, M., Polarized memory effect observed on amorphous selenium thin films, Jpn. J. Appl. Phys. 11 (1972) 606.	
	CI4	Mazurier, F.; Levy, M.; Souquet, J.L., Reversible and irreversible electrical switching in TeO <sub>2</sub> -V <sub>2</sub> O <sub>5</sub> based glasses, Journal de Physique IV 2 (1992) C2-185 - C2-188.	
	CJ4	McHardy et al., The dissolution of metals in amorphous chalcogenides and the effects of electron and ultraviolet radiation, 20 J. PHYS. C: SOLID STATE PHYS., pp. 4055-4075 (1987).	
	CK4	Messoussi, R.; Bernede, J.C.; Benhida, S.; Abachi, T.; Latef, A., Electrical characterization of M/Se structures (M=Ni, Bi), Mat. Chem. And Phys. 28 (1991) 253-258.	
	CL4	Mitkova, M.; Boolchand, P., Microscopic origin of the glass forming tendency in chalcogenides and constraint theory, J. Non-Cryst. Solids 240 (1998) 1-21.	
	CM4	Mitkova, M.; Kozicki, M.N., Silver incorporation in Ge-Se glasses used in programmable metallization cell devices, J. Non-Cryst. Solids 299-302 (2002) 1023-1027.	
	CN4	Mitkova, M.; Wang, Y.; Boolchand, P., Dual chemical role of Ag as an additive in chalcogenide glasses, Phys. Rev. Lett. 83 (1999) 3848-3851.	
	CO4	Miyatani, S.-y., Electronic and ionic conduction in (AgxCu <sub>1-x</sub> ) <sub>2</sub> Se, J. Phys. Soc. Japan 34 (1973) 423-432.	
	CP4	Miyatani, S.-y., Electrical properties of Ag <sub>2</sub> Se, J. Phys. Soc. Japan 13 (1958) 317.	

Christina Wilson 5/11/04



Substitute for form 1449B/PTO		Complete if Known	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		Application Number	To be assigned 12/66602
		Filing Date	Currently Herewith 9/12/03
		First Named Inventor	John T. Moore
		Prior Group Art Unit	2824
		Prior Examiner Name	M. Lohrs C. Wilson
Sheet 8 of 10	Attorney Docket Number	M4065.0693/P693-A	

QW	CQ4	Miyatani, S.-y., Ionic conduction in beta-Ag <sub>2</sub> Te and beta-Ag <sub>2</sub> Se, Journal Phys. Soc. Japan 14 (1959) 996-1002.	
	CR4	Mizusaki et al., Kinetic Studies on the Selenization of Silver, 47 Bull. Chem. Soc. Japan, No. 11, pp. 2851-2855 (November 1974).	
	CS4	Mott, N.F., Conduction in glasses containing transition metal ions, J. Non-Cryst. Solids 1 (1968) 1-17.	
	CT4	Nakayama, K.; Kitagawa, T.; Ohmura, M.; Suzuki, M., Nonvolatile memory based on phase transitions in chalcogenide thin films, Jpn. J. Appl. Phys. 32 (1993) 564-569.	
	CU4	Nakayama, K.; Kojima, K.; Hayakawa, F.; Imai, Y.; Kitagawa, A.; Suzuki, M., Submicron nonvolatile memory cell based on reversible phase transition in chalcogenide glasses, Jpn. J. Appl. Phys. 39 (2000) 6157-6161.	
	CV4	Nang, T.T.; Okuda, M.; Matsushita, T.; Yokota, S.; Suzuki, A., Electrical and optical parameters of GeSe <sub>1-x</sub> amorphous thin films, Jap. J. App. Phys. 15 (1976) 849-853.	
	CW4	Narayanan, R.A.; Asokan, S.; Kumar, A., Evidence concerning the effect of topology on electrical switching in chalcogenide network glasses, Phys. Rev. B 54 (1996) 4413-4415.	
	CX4	Neale, R.G.; Aseltine, J.A., The application of amorphous materials to computer memories, IEEE transactions on electron dev. Ed-20 (1973) 195-209.	
	CY4	Ovshinsky S.R.; Fritzsche, H., Reversible structural transformations in amorphous semiconductors for memory and logic, Metallurgical transactions 2 (1971) 641-645.	
	CZ4	Ovshinsky, S.R., Reversible electrical switching phenomena in disordered structures, Phys. Rev. Lett. 21 (1968) 1450-1453.	
	CA5	Owen, A.E.; LeComber, P.G.; Sarabayrouse, G.; Spear, W.E., New amorphous-silicon electrically programmable nonvolatile switching device, IEE Proc. 129 (1982) 51-54	
	CB5	Owen, A.E.; Firth, A.P.; Ewen, P.J.S., Photo-induced structural and physico-chemical changes in amorphous chalcogenide semiconductors, Phil. Mag. B 52 (1985) 347-362.	
	CC5	Owen, A.E.; LeComber, P.G.; Hajto, J.; Rose, M.J.; Snell, A.J., Switching in amorphous devices, Int. J. Electronics 73 (1992) 897-906.	
	CD5	Owen et al., Metal-Chalcogenide Photoresists for High Resolution Lithography and Sub-Micron Structures, NANOSTRUCTURE PHYSICS AND FABRICATION, pp. 447-451 (M. Reed ed. 1989).	
	CE5	Pearson, A.D.; Miller, C.E., Filamentary conduction in semiconducting glass diodes, App. Phys. Lett. 14 (1969) 280-282.	
	CF5	Pinto, R.; Ramanathan, K.V., Electric field induced memory switching in thin films of the chalcogenide system Ge-As-Se, Appl. Phys. Lett. 19 (1971) 221-223.	
	CG5	Popescu, C., The effect of local non-uniformities on thermal switching and high field behavior of structures with chalcogenide glasses, Solid-state electronics 18 (1975) 671-681.	
	CH5	Popescu, C.; Croitoru, N., The contribution of the lateral thermal instability to the switching phenomenon, J. Non-Cryst. Solids 8-10 (1972) 531-537.	
	CI5	Popov, A.I.; Geller, I.KH.; Shemetova, V.K., Memory and threshold switching effects in amorphous selenium, Phys. Stat. Sol. (a) 44 (1977) K71-K73.	
	CJ5	Prakash, S.; Asokan, S.; Ghare, D.B., Easily reversible memory switching in Ge-As-Te glasses, J. Phys. D: Appl. Phys. 29 (1996) 2004-2008.	
	CK5	Rahman, S.; Sivarama Sastry, G., Electronic switching in Ge-Bi-Se-Te glasses, Mat. Sci. and Eng. B12 (1992) 219-222.	
	CL5	Ramesh, K.; Asokan, S.; Sangunni, K.S.; Gopal, E.S.R., Electrical Switching in germanium telluride glasses doped with Cu and Ag, Appl. Phys. A 69 (1999) 421-425.	
	CM5	Rose, M.J.; Hajto, J.; LeComber, P.G.; Gage, S.M.; Choi, W.K.; Snell, A.J.; Owen, A.E., Amorphous silicon analogue memory devices, J. Non-Cryst. Solids 115 (1989) 168-170.	
	CN5	Rose, M.J.; Snell, A.J.; LeComber, P.G.; Hajto, J.; Fitzgerald, A.G.; Owen, A.E., Aspects of non-volatility in a -Si:H memory devices, Mat. Res. Soc. Symp. Proc. V 258, 1992, 1075-1080.	
	CO5	Safran et al., TEM study of Ag <sub>2</sub> Se developed by the reaction of poly crystalline silver films and selenium, 317 Thin Solid Films, pp. 72-76 (1998).	
QW	CP5	Schwocker, D.; Rieder, G., On the reliability of amorphous chalcogenide switching devices, J.	

Christian Wilson

5/11/04

Substitute for form 1449B/PTO		<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		Application Number	To be assigned 10/660602
		Filing Date	Currently Herewith 9/12/03
		First Named Inventor	John T. Moore
		Prior Group Art Unit	2824
		Prior Examiner Name	M. Luhrs C. Wilson
Sheet 9 of 10	Attorney Docket Number	M4065.0693/P693-A	

		Non-Cryst. Solids 29 (1978) 397-407.	
	CQ5	Sharma, A.K.; Singh, B., Electrical conductivity measurements of evaporated selenium films in vacuum, Proc. Indian Natn. Sci. Acad. 46, A, (1980) 362-368.	
	CR5	Sharma, P., Structural, electrical and optical properties of silver selenide films, Ind. J. Of pure and applied phys. 35 (1997) 424-427.	
	CS5	Shimizu et al., The Photo-Erasable Memory Switching Effect of Ag Photo-Doped Chalcogenide Glasses, 46 B. CHEM SOC. JAPAN, No. 12, pp. 3662-3365 (1973).	
	CT5	Snell, A.J.; Lecomber, P.G.; Hajto, J.; Rose, M.J.; Owen, A.E.; Osborne, I.L., Analogue memory effects in metal/a-Si:H/metal memory devices, J. Non-Cryst. Solids 137-138 (1991) 1257-1262.	
	CU5	Snell, A.J.; Hajto, J.; Rose, M.J.; Osborne, I.S.; Holmes, A.; Owen, A.E.; Gibson, R.A.G., Analogue memory effects in metal/a-Si:H/metal thin film structures, Mat. Res. Soc. Symp. Proc. V 297, 1993, 1017-1021.	
	CV5	Somogyi et al., Temperture Dependence of the Carrier Mobility in Ag <sub>2</sub> Se Layers Grown on NaCl and SiO <sub>2</sub> Substrates, 74 Acta Physica Hungarica, No. 3, pp. 243-255 (1994).	
	CW5	Steventon, A.G., Microfilaments in amorphous chalcogenide memory devices, J. Phys. D: Appl. Phys. 8 (1975) L120-L122.	
	CX5	Steventon, A.G., The switching mechanisms in amorphous chalcogenide memory devices, J. Non-Cryst. Solids 21 (1976) 319-329.	
	CY5	Stocker, H.J., Bulk and thin film switching and memory effects in semiconducting chalcogenide glasses, App. Phys. Lett. 15 (1969) 55-57.	
	CZ5	Tai et al., Multilevel Ge-Se film based resist systems, SPIE Vol. 333 Submicron Lithography, pp. 32-39 (March 1982).	
	CA6	Tai et al., Submicron optical lithography using an inorganic resist/polymer bilevel scheme, 17 J. Vac. Sci. Technol., No. 5, pp. 1169-1176 (Sept./Oct. 1980).	
	CB6	Tanaka, K., Ionic and mixed conductions in Ag photodoping process, Mod. Phys. Lett B 4 (1990) 1373-1377.	
	CC6	Tanaka, K.; Iizima, S.; Sugi, M.; Okada, Y.; Kikuchi, M., Thermal effects on switching phenomenon in chalcogenide amorphous semiconductors, Solid State Comm. 8 (1970) 387-389.	
	CD6	Thornburg, D.D., Memory switching in a Type I amorphous chalcogenide, J. Elect. Mat. 2 (1973) 3-15.	
	CE6	Thornburg, D.D., Memory switching in amorphous arsenic triselenide, J. Non-Cryst. Solids 11 (1972) 113-120.	
	CF5	Thornburg, D.D.; White, R.M., Electric field enhanced phase separation and memory switching in amorphous arsenic triselenide, Journal(?) (1972) 4609-4612.	
	CG5	Tichy, L.; Ticha, H., Remark on the glass-forming ability in GexSe1-x and AsxSe1-x systems, J. Non-Cryst. Solids 261 (2000) 277-281.	
	CH6	Titus, S.S.K.; Chatterjee, R.; Asokan, S., Electrical switching and short-range order in As-Te glasses, Phys. Rev. B 48 (1993) 14650-14652.	
	CI6	Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.; Lagarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and exafs structural investigation, Transport-structure relations in fast ion and mixed conductors Proceedings of the 6th Riso International symposium. 9-13 September 1985.	
	CJ6	Tregouet, Y.; Bernede, J.C., Silver movements in Ag <sub>2</sub> Te thin films: switching and memory effects, Thin Solid Films 57 (1979) 49-54.	
	CK6	Uemura, O.; Kameda, Y.; Kokai, S.; Satow, T., Thermally induced crystallization of amorphous Ge <sub>0.4</sub> Se <sub>0.6</sub> , J. Non-Cryst. Solids 117-118 (1990) 219-221.	
	CL6	Uttecht, R.; Stevenson, H.; Sie, C.H.; Griener, J.D.; Raghavan, K.S., Electric field induced filament formation in As-Te-Ge glass, J. Non-Cryst. Solids 2 (1970) 358-370.	
	CM6	Viger, C.; Lefrancois, G.; Fleury, G., Anomalous behaviour of amorphous selenium films, J. Non-Cryst. Solids 33 (1976) 267-272.	
	CN6	Vodenicharov, C.; Parvanov, S.; Petkov, P., Electrode-limited currents in the thin-film M-GeSe-	

Christian Wilson

5/11/04

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449B/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		<b>Complete if Known</b>			
		Application Number	To be assigned 10/660602		
		Filing Date	Currently Herewith 9/12/03		
		First Named Inventor	John T. Moore		
		Prior Group Art Unit	2824		
		Prior Examiner Name	M. Luthrs C. Wilson		
Sheet	10	of	10	Attorney Docket Number	M4065.0693/P693-A

OW		M system, Mat. Chem. And Phys. 21 (1989) 447-454.	
	CO6	Wang, S.-J.; Misium, G.R.; Camp, J.C.; Chen, K.-L.; Tigelaar, H.L., High-performance Metal/silicide antifuse, IEEE electron dev. Lett. 13 (1992) 471-472.	
	CP6	Weirauch, D.F., Threshold switching and thermal filaments in amorphous semiconductors, App. Phys. Lett. 16 (1970) 72-73.	
	CQ6	West, W.C.; Sieradzki, K.; Kardynal, B.; Kozicki, M.N., Equivalent circuit modeling of the Ag/As <sub>0.24</sub> S <sub>0.36</sub> Ag <sub>0.40</sub> /Ag System prepared by photodissolution of Ag, J. Electrochem. Soc. 145 (1998) 2971-2974	
	CT6	West, W.C., Electrically erasable non-volatile memory via electrochemical deposition of multifractal aggregates, Ph.D. Dissertation, ASU 1998	
	CU6	Yoshikawa, et al., A new inorganic electron resist of high contrast, 31 App. Phys. Lett., No. 3, pp. 161-163 (August 1977).	
OW	CV6	Zhang, M.; Mancini, S.; Bresser, W.; Boolchand, P., Variation of glass transition temperature, T <sub>g</sub> , with average coordination number, <m>, in network glasses: evidence of a threshold behavior in the slope  dT <sub>g</sub> /d<m>  at the rigidity percolation threshold (<m>=2.4), J. Non-Cryst. Solids 151 (1992) 149-154.	

Examiner Signature	Christian Wilson	Date Considered	5/11/04
--------------------	------------------	-----------------	---------

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup>Applicant's unique citation designation number (optional). <sup>2</sup>Applicant is to place a check mark here if English language Translation is attached.